ERRATA

Erratum: Surface-dimer and bulk-atom imaging of the Si(001) (2×1) surface by Kikuchi electron holography

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Figure 6(b) in our paper is wrong. The correct figure is shown below.

![Correct Figure 6(b)](image)

We have found that the quality of Fig. 4 in this paper is not clear. A better-quality figure is reproduced below.

![Better-quality Figure 4](image)

FIG. 6(a). The side-view atomic images along [110] direction and cut through the emitter for a normal-incident configuration. (b) The top-view atomic images at the dimer plane for the same configuration as (a). These images are reconstructed from 48 Kikuchi patterns (218-548 eV).

FIG. 4. The side-view reconstructed images of Si(001) (2×1) surface cut through the emitter and along (a) [110] direction and (b) [010] direction. The thick cross marks the position of the emitter. The images are reconstructed from the same energy range as Fig. 3.

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Erratum: Ab initio study of hydrogen adsorption on the Si(111)-(7×7) surface

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[S0163-1829(96)04732-7]

In our paper on the theory of hydrogen adsorption on the Si(111)-(7×7) surface we mentioned the experimental work of Avouris and Wolkow (see Ref. 2) as relevant to the study of chemical reactivity on this surface. Regrettably, we missed how closely the theoretical results resemble some of the conclusions drawn by Avouris and Wolkow on the charge transfer effects. Even though the experimental work was on NH₃ reactions with the Si(111)-(7×7) surface, and our theoretical treatment involved single H atoms, the charge transfer mechanisms are essentially identical and were fully anticipated by the work of Avouris and Wolkow. In retrospect, it is satisfying to find such close agreement between theory and experiment. We regret this unfortunate omission in our paper.

Erratum: Grain-boundary dissociation by the emission of stacking faults

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[S0163-1829(96)02731-2]

This Erratum draws attention to three problems.
1. The references for this paper were misnumbered: the number for each reference should be increased by one to correspond to the citation numbers in the text.
2. The term “special” boundary in the first and second paragraphs of page R4242 should be replaced by “singular” boundary.
3. Figure 3 is reprinted here in a larger form to better show the details that are difficult to see in the originally published version.

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(ii) Our Fig. 3(a) was printed twice. It should have been shown only once, on p. R4247. Figure 3 is correct as it appeared. This Erratum applies only to the paper version of the journal. In the on-line rapid communications journal the paper is correct and complete.

FIG. 1. (a) Occupied-state image (161×192 Å) and (b) the height profile (Å) measured along a cross line perpendicular to the dimer-row direction of an unirradiated Si(100)-(2×1) surface.

FIG. 2. (a) Occupied-state image (161×192 Å) and (b) the height profile (Å) measured along a cross line (110) direction of a Si(100) surface that has been irradiated by one pulse of laser with a fluence of 150 mJ/cm².

Erratum: Electronic structure and stability of the α-Sn/InSb(111)A nonpolar-polar heterojunction interface

Kazuo Yamamoto and Kazuaki Kobayashi
[S0163-1829(96)09831-1]

The title of our paper was inadvertently misprinted during the publication process. “EPC” should not be part of the title.